





BAV19WS-BAV21WS SWITCHING DIODE



Features

- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion
- For General Purpose Switching Applications
- High Conductance
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Schematic & Pin Configuration



Mechanical Characteristics

- Case: SOD-323, Molded plastic
- Terminals: Plated leads solderable per MIL-STD-202, Method 208

Maximum Ratings@T_A=25°C unless otherwise specified

Characteristic	Symbol	BAV19WS	BAV20WS	BAV21WS	Unit
Marking Code		A8	T2	Т3	
Non-Repetitive Peak Reverse Voltage	V _{RM}	120	200	250	V
Peak Repetitive Peak Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	100	150	200	V
RMS Reverse Voltage	V _{R(RMS)}	71	106	141	
Average Rectified Output Current	Io		200		mA
Forward continuous current	I _{FM}	400			mA
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method) @t=1.0ms @t=1.0s	IFSM	2.5 0.5			А
Power Dissipation	P _d		250		mW
Repetitive Peak Forward Current	I _{FRM}	625		mA	
Typical Thermal Resistance Junction to Ambient	R _{θJA}	500		°C/W	
Junction Temperature Range	TJ	150		°C	
Storage Temperature Range	T _{STG}	-55 to +150		°C	

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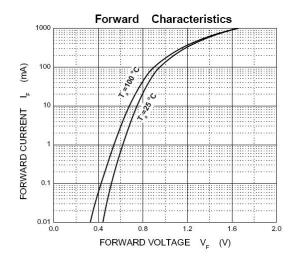


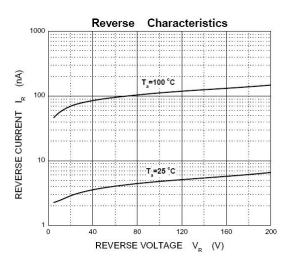
Electrical Characteristics@T_A=25°C unless otherwise specified

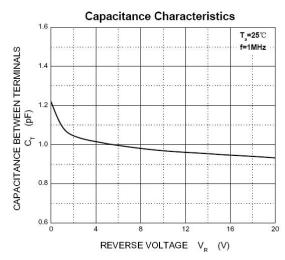
Characteristic	Symbol	Test Condition	Min	Тур	Max	Unit
Forward Voltage*	V _F	I _F =100mA I _F =200mA	-	0.95 1.06	1.00 1.25	V
Reverse Leakage Current* BAV19WS BAV20WS BAV21WS	IR	V _R =100V V _R =150V V _R =200V	-	0.007	0.1	μA
Diode capacitance	Ст	V _R =0V,f=1.0MHz	-	1.2	5	pF
Reverse recovery time	t _{rr}	$I_F = I_R = 30 \text{mA}, I_{rr} = 0.1 \times I_R, R_L = 100 \Omega$	-	-	50	ns

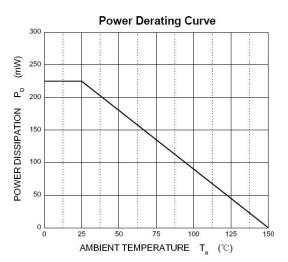
^{*} Pulse width < 300 µs, duty cycle < 2%

Ratings and Characteristics Curves









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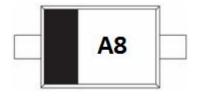


Ordering Information

Device	Package	Shipping
BAV19WS-BAV21WS	SOD-323 (Pb-Free)	3000pcs / reel

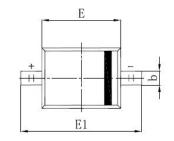
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

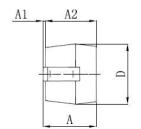
Marking Diagram

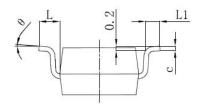


A8 = Marking Code

Mechanical Dimensions SOD-323

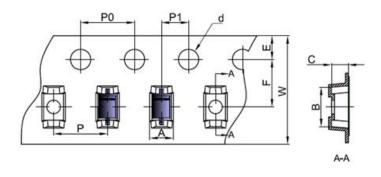






Millimeters		neters	Inches		
SYMBOL	MIN.	MAX.	MIN.	MAX.	
Α	-	1.000	-	0.039	
A1	0.000	0.100	0.000	0.004	
A2	0.800	0.900	0.031	0.035	
b	0.250	0.350	0.010	0.014	
С	0.080	0.150	0.003	0.006	
D	1.200	1.400	0.047	0.055	
Е	1.600	1.800	0.063	0.071	
E1	2.500	2.700	0.098	0.106	
L	0.475 REF.		0.019 REF.		
L1	0.250	0.400	0.010	0.016	
θ	0°	8°	0°	8°	

Carrier Tape Specification SOD-323



SYMB	Millimeters		
OL	Min.	Max.	
В	2.85	2.95	
С	1.20	1.30	
d	1.40	1.60	
E	1.65	1.85	
F	3.40	3.60	
Р	3.90	4.10	
P0	3.90	4.10	
P1	1.90	2.10	
W	7.90	8.30	

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